

Benjamin Olson

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

15 papers	439 citations	11 h-index	16 g-index
16 ext. papers	499 ext. citations	3.1 avg, IF	2.82 L-index

#	Paper	IF	Citations
15	Time-resolved optical measurements of minority carrier recombination in a mid-wave infrared InAsSb alloy and InAs/InAsSb superlattice. <i>Applied Physics Letters</i> , 2012 , 101, 092109	3.4	154
14	Identification of dominant recombination mechanisms in narrow-bandgap InAs/InAsSb type-II superlattices and InAsSb alloys. <i>Applied Physics Letters</i> , 2013 , 103, 052106	3.4	59
13	Effects of layer thickness and alloy composition on carrier lifetimes in mid-wave infrared InAs/InAsSb superlattices. <i>Applied Physics Letters</i> , 2014 , 105, 022107	3.4	52
12	All-optical measurement of vertical charge carrier transport in mid-wave infrared InAs/GaSb type-II superlattices. <i>Applied Physics Letters</i> , 2013 , 102, 202101	3.4	23
11	Auger recombination in long-wave infrared InAs/InAsSb type-II superlattices. <i>Applied Physics Letters</i> , 2015 , 107, 261104	3.4	21
10	Enhanced infrared detectors using resonant structures combined with thin type-II superlattice absorbers. <i>Applied Physics Letters</i> , 2016 , 109, 251103	3.4	21
9	Bandgap and temperature dependence of Auger recombination in InAs/InAsSb type-II superlattices. <i>Journal of Applied Physics</i> , 2016 , 119, 215705	2.5	20
8	Temperature-dependent optical measurements of the dominant recombination mechanisms in InAs/InAsSb type-II superlattices. <i>Journal of Applied Physics</i> , 2015 , 118, 125701	2.5	19
7	Minority carrier lifetime and dark current measurements in mid-wavelength infrared InAs _{0.91} Sb _{0.09} alloy nBn photodetectors. <i>Applied Physics Letters</i> , 2015 , 107, 183504	3.4	18
6	Effects of electron doping level on minority carrier lifetimes in n-type mid-wave infrared InAs/InAs _{1-x} Sb _x type-II superlattices. <i>Applied Physics Letters</i> , 2016 , 109, 261105	3.4	17
5	Post growth annealing study on long wavelength infrared InAs/GaSb superlattices. <i>Journal of Applied Physics</i> , 2012 , 111, 053113	2.5	14
4	Far infrared edge photoresponse and persistent edge transport in an inverted InAs/GaSb heterostructure. <i>Applied Physics Letters</i> , 2016 , 108, 013106	3.4	8
3	Optical and electrical properties of narrow-bandgap infrared W-structure superlattices incorporating AlAs/AlSb/AlAs barrier layers. <i>Applied Physics Letters</i> , 2016 , 108, 252104	3.4	6
2	Demonstration of long minority carrier lifetimes in very narrow bandgap ternary InAs/GaInSb superlattices. <i>Applied Physics Letters</i> , 2015 , 107, 131102	3.4	6
1	Contactless measurement of equilibrium electron concentrations in n-type InAs/InAs _{1-x} Sb _x type-II superlattices. <i>Applied Physics Letters</i> , 2016 , 109, 022105	3.4	1